HD32141
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Designed for EMI/RFI, lab, HIRF, radar, TWT driver, high power pulse applications, or EMI/RFI, lab, Pulse, and all communication applications
Small form factor, rack mounted system
Class AB Linear high power advanced technology design
Suitable for S-Band high power linear pulse applications
Built-in protection circuits, with extensive monitoring
Local LCD & remote flexible interfaces
High efficiency, with unprecedented reliability and ruggedness



ELECTRICAL SPECIFICATIONS : 50Ω, 25°C

Parameter	Specification			Notes	
Operating Frequency	9.6 - 9.9 GHz				
Power Output @ Peak Pulse	1000 Watt Min				
Pulse Characteristics	**Width**	**Duty**	**PRF**	**Rise/Fall**	**Droop**
	up to 50 µS	10 % Max	Up to 10.0 KHz	<100 nS	<1 dB
Power Gain	60 dB Min			0dBm or less for rated Pout	
Power Gain Flatness	2.0 dB p-p Max			Constant input power	
Gain Adjustment Range	20 dB Min			Local or remote capable	
Input Return Loss	-10 dB Max				
Output Power On/Off Ratio	-80 dB Max			TTL Gate Control	
Spurious	-60 dBc Max			Non-harmonic	
Harmonics	-30 dBc Typ			At rated output power	
Operating Voltage	100 - 240 VAC, 50 - 60Hz				
Power Consumption	1200 Watt Avg. Max			@ 10% Duty cycle	
Input Power Protection	+3 dBm Max[1]				
Load VSWR Protection	4 : 1: Max[2]			Foldback @ preset limit	
Sample Port (optional)	-60 dBc			N-Female	

1 Units with optional digital monitor and control, for basic units <10 Sec without damage
2 Units with optional digital monitor and control, for basic units <1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	up to 95 %	Non Condensing
Altitude	3000 meters	
Shock & Vibration	Normal transport[3]	

3 MIL Spec available for quotation

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	482 x 219 x 700 mm	5U, excluding handles
Weight	20Kg. Max	
RF Conn. In / Out / Sample (optional)	Type-N Female/WR112/Type-N-Female	Rear panel std. (Front avail.)
Gate Control	BNC Female	Rear panel std. (Front avail.)
AC Power / Interface Connector	IEC 60320-C14 / 9-Pin D-Sub	Or equivalent
Cooling	Built in Fan Cooling	Variable speed
OPTIONAL: Digital Monitor & Control (DMC) FWD, REV, VSWR, GAIN, ALC, V & I, TEMP, Optional Safety Interlock (INT)	Ethernet RJ-45 TCP/IP, RS422/485, USB Optional GPIB Interface Open=STBY/Short=RFON	 IEEE rear panel BNC-F rear panel

4 Chassis depth may increase to 750mm with Option DMC.

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Specifications subject to change without notice.
Specifications and drawings may vary with selected options.

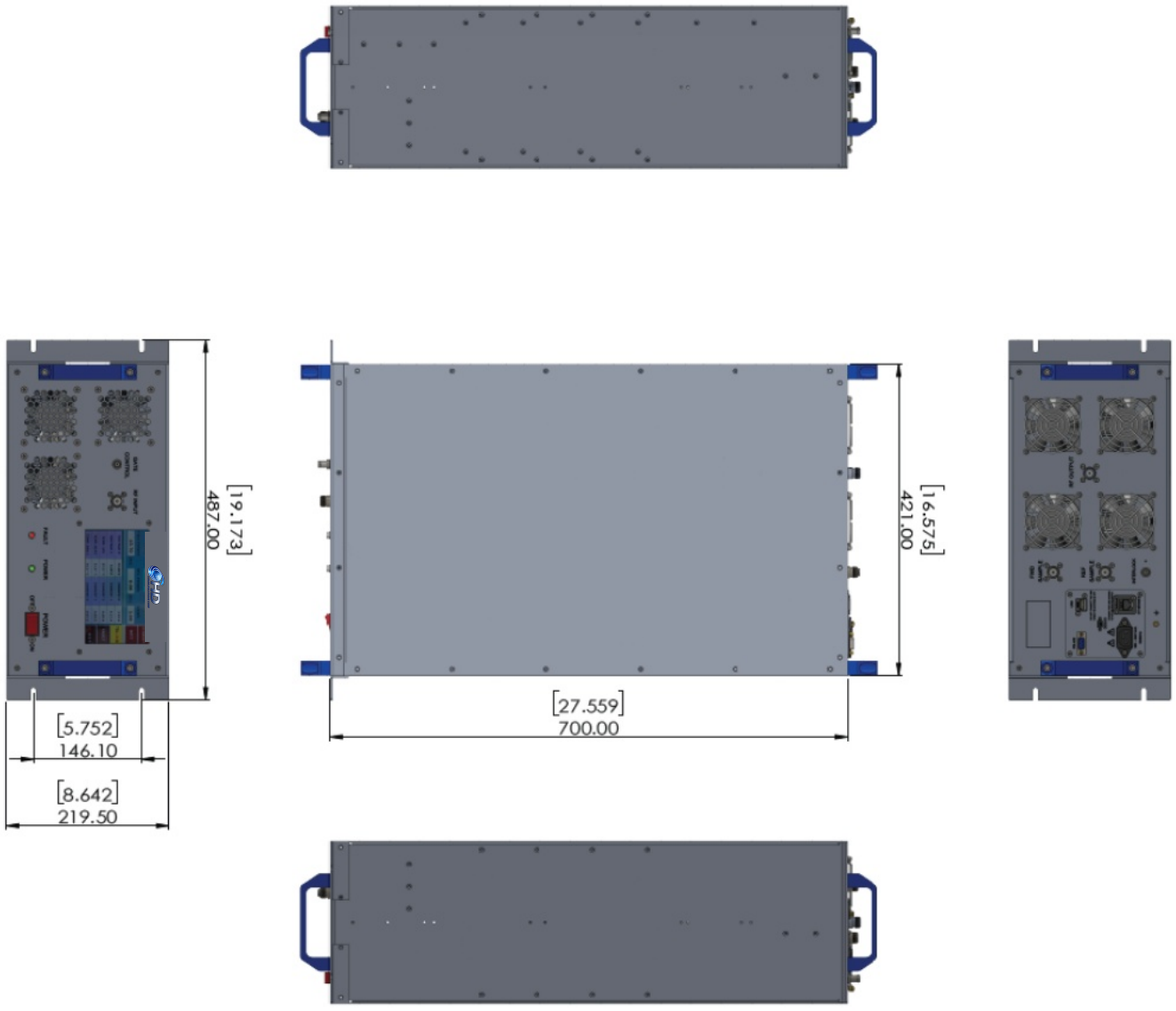
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AVAILABLE SPECIAL OPTIONS

Parameter	Specification	Notes
Option FRS: Forward RF Sample	-60dB, Type N-Female	Rear panel std. (Front avail.)
Option RRS: Reflected RF Sample	-50dB, Type N-Female	Rear panel std. (Front avail.)
Option GPIB: GPIB remote control	GPIB IEEE-488 Remote capability	
Included CPM: Calibrated Power Monitoring (With purchase of Option DMC)	Offset correction entry for +/- 0.2dB accuracy	4-points standard[5]

5 Consult with factory if additional points would be required.

OUTLINE DRAWING
SHOWN WITH LCD DIGITAL CONTROLLER



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